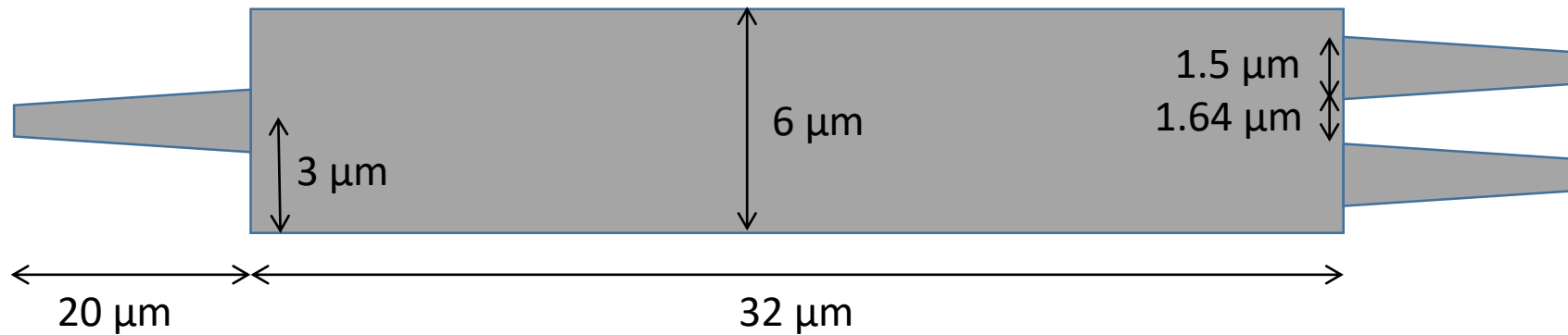


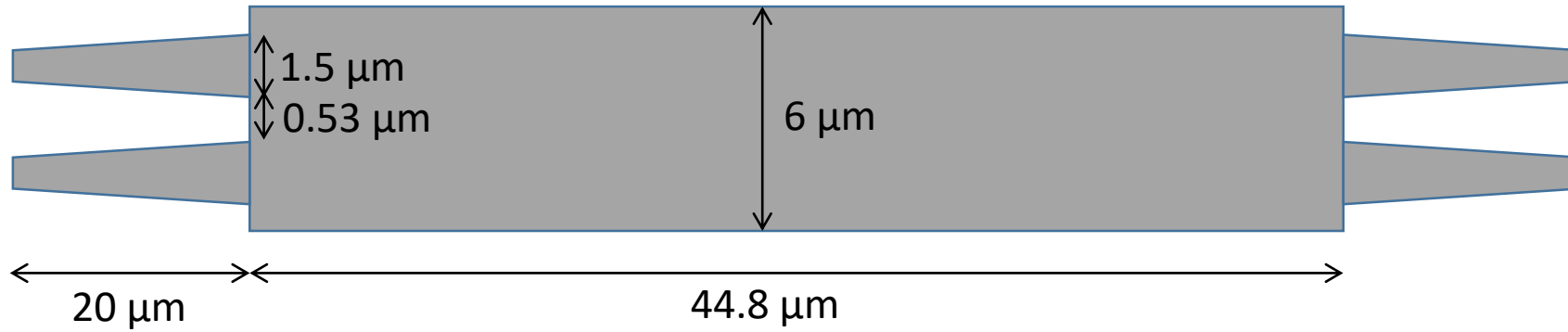


CORNERSTONE Device Dimensions for 220 nm SOI Platform $\lambda = 1550$ nm

Rib waveguide etch depth = 120 nm
Grating etch depth = 70 nm

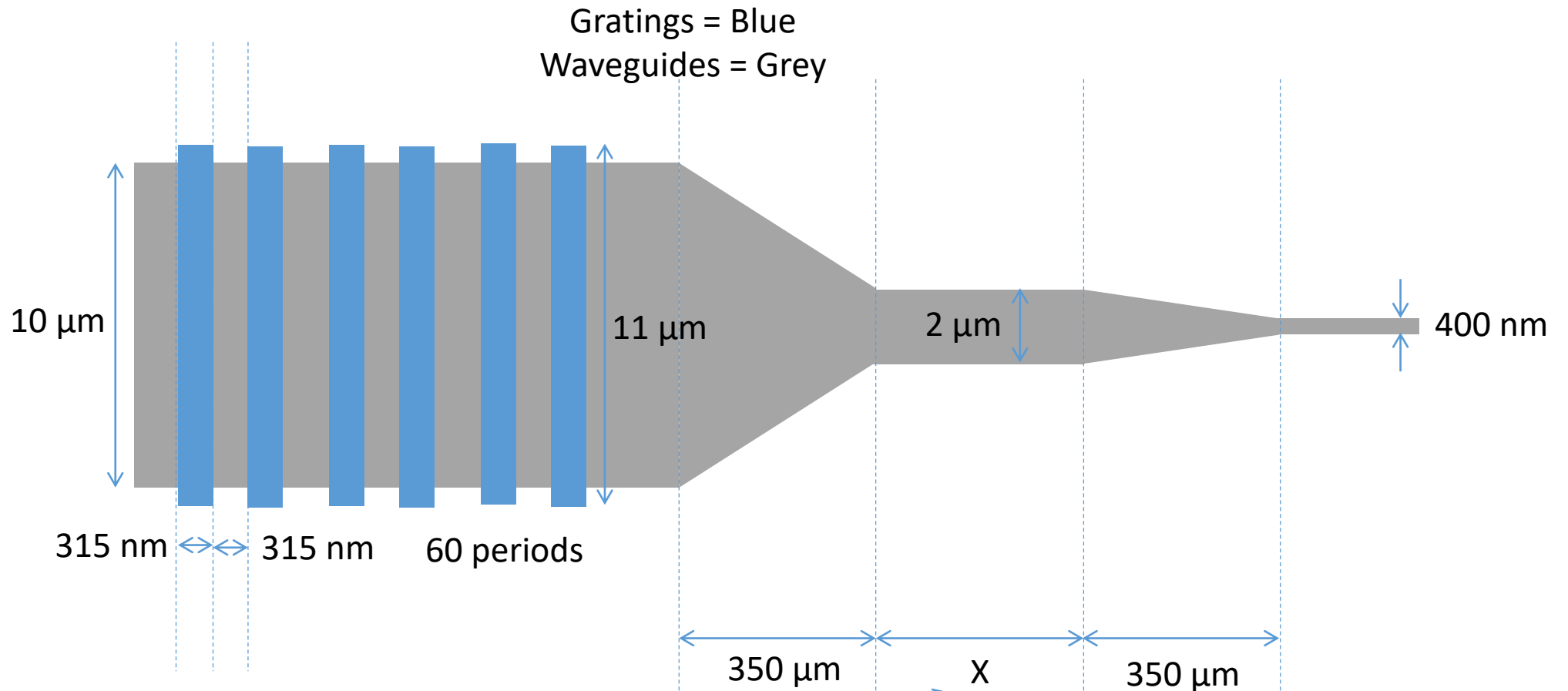


*Add rib protect layer in GDS file



*Add rib protect layer in GDS file

Grating couplers (etch depth = 70 nm)



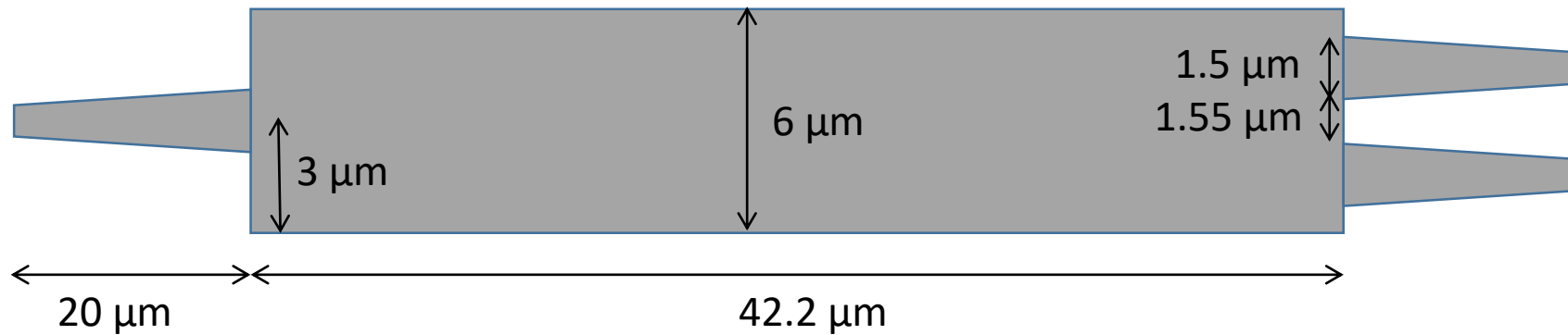
Use waveguide of width X for low loss routing to devices if required

*Add rib protect layer in GDS file

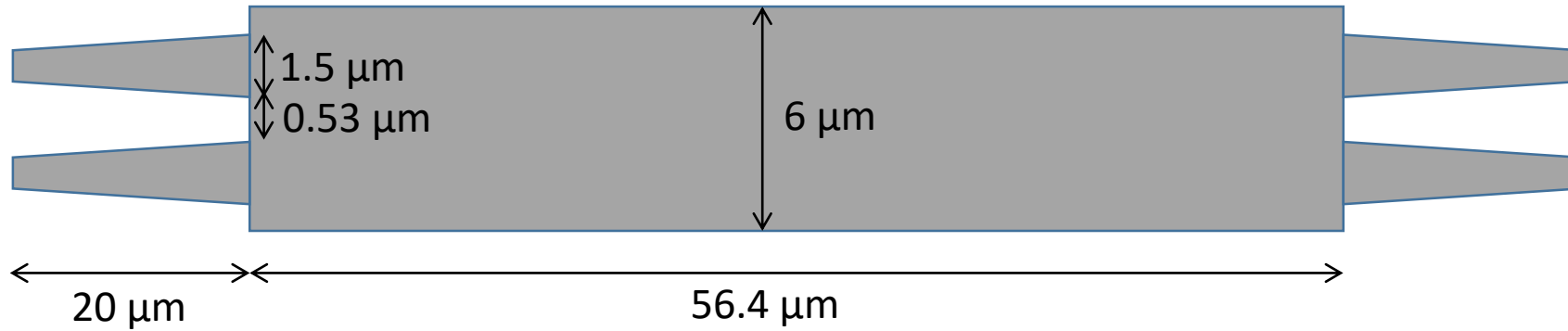


CORNERSTONE Device Dimensions for 220 nm SOI Platform $\lambda = 1310$ nm

Rib waveguide etch depth = 120 nm
Grating etch depth = 70 nm

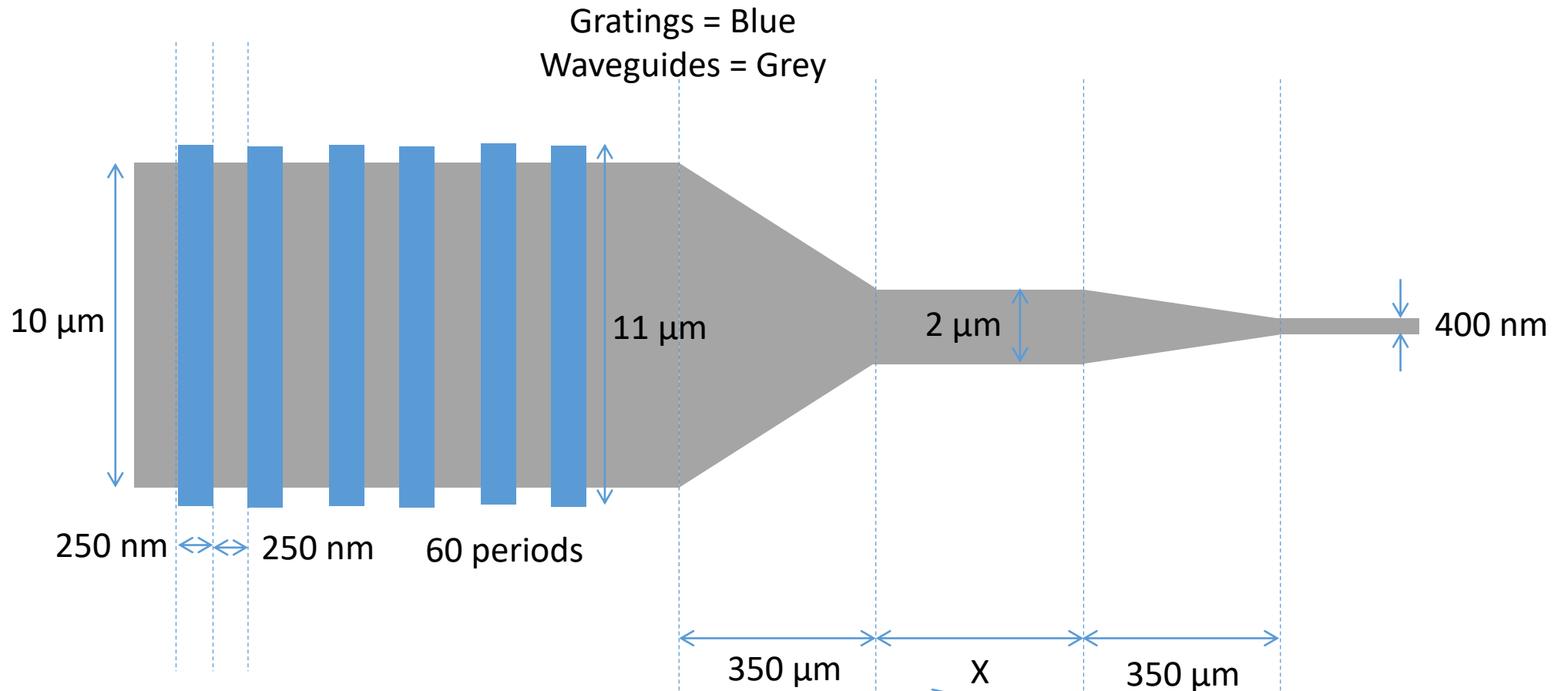


*Add rib protect layer in GDS file



*Add rib protect layer in GDS file

Grating couplers (etch depth = 70 nm)



Use waveguide of width X for low loss routing to devices if required

*Add rib protect layer in GDS file